

PBSS5350TH 50 V, 3 A PNP low VCEsat (BISS) transistor 21 June 2017

Product data sheet

1. General description

PNP low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package.

2. Features and benefits

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability: I_C and I_{CM}
- High collector current gain (h_{FE}) at high I_C
- Higher efficiency leading to less heat genereation
- High temperature applications up to 175 °C
- AEC-Q101 qualified

3. Applications

- Power management
- DC-to-DC conversion
- Supply line switches
- Battery charger switches
- Peripheral drivers
- Driver in low supply voltage applications (e.g. lamps and LEDs)
- Inductive load driver

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base		-	-	-50	V
I _C	collector current			-	-	-2	Α
I _{CM}	peak collector current	pulsed	[1]	-	-	-3	Α
		single pulse; t _p < 1 ms		-	-	-5	Α
R _{CEsat}	collector-emitter saturation resistance	$I_C = -2 \text{ A}$; $I_B = -200 \text{ mA}$; $T_{amb} = 25 \text{ °C}$	[2]	-	-	135	mΩ

- [1] Pulse conditions: pulse width $t_p \le 100$ ms; duty cycle $\delta \le 0.25$
- [2] Pulse test: $t_p \le 300 \mu s$; $\delta \le 0.02$



5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	3	C
2	Е	emitter		В
3	С	collector	1 2 TO-236AB (SOT23)	E sym132

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PBSS5350TH	TO-236AB	plastic surface-mounted package; 3 leads	SOT23

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
PBSS5350TH	FJ%

[1] % = placeholder for manufacturing site code

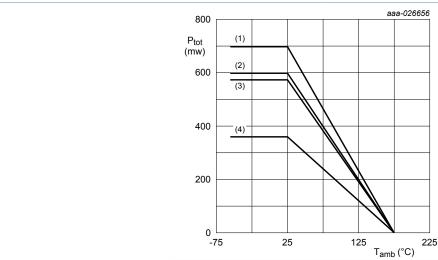
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter		-	-50	V
V_{CEO}	collector-emitter voltage	open base		-	-50	V
V _{EBO}	emitter-base voltage	open collector		-	-7	V
I _C	collector current			-	-2	Α
I _{CM}	peak collector current	pulsed	[1]	-	-3	Α
		single pulse; t _p < 1 ms		-	-5	Α
I _B	base current			-	-500	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[2]	-	360	mW
			[3]	-	575	mW
			[4]	-	600	mW
			[5]	-	700	mW
			[1] [2]	-	1.44	W
Tj	junction temperature			-	175	°C
T _{amb}	ambient temperature			-55	175	°C
T _{stg}	storage temperature			-65	175	°C

- [1] Pulse conditions: pulse width $t_p \le 100$ ms; duty cycle $\delta \le 0.25$
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.
- [5] Device mounted on an FR4 PCB, 4-layer copper, tin-plated, mounting pad for collector 1 cm².



- (1) FR4 PCB, 4-layer copper, 1 cm²
- (2) FR4 PCB, 4-layer copper, standard footprint
- (3) FR4 PCB, single sided copper, 1 cm²
- (4) FR4 PCB, single sided copper, standard footprint

Fig. 1. Power derating curves for SOT23

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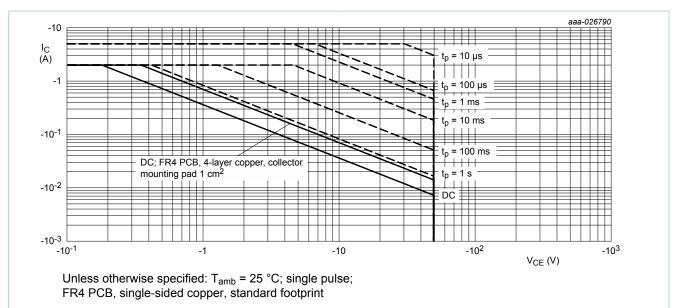


Fig. 2. Safe operating area; junction to ambient; continuous and peak drain currents as a function of collectoremitter voltage

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
uily a)	thermal resistance		[1]	-	-	417	K/W
	from junction to ambient		[2]	-	-	261	K/W
			[3]	-	-	250	K/W
			[4]	-	-	215	K/W
			[1] [5]	-	-	104	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	75	-	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- [3] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.
- [4] Device mounted on an FR4 PCB, 4-layer copper, tin-plated, mounting pad for collector 1 cm².
- [5] Operated under pulse conditions: pulse width $t_p \le 100$ ms; duty cycle $\delta \le 0.25$

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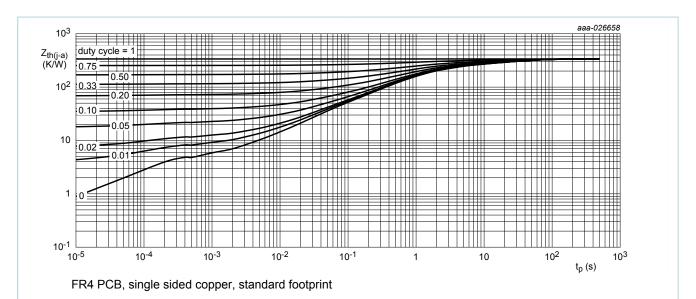


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

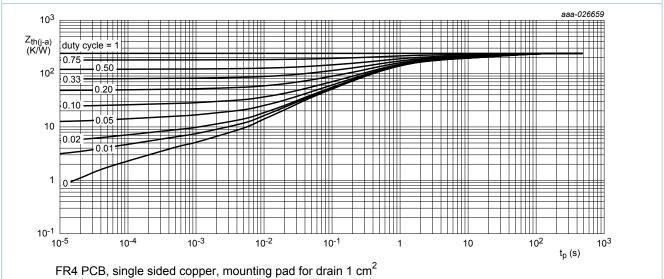


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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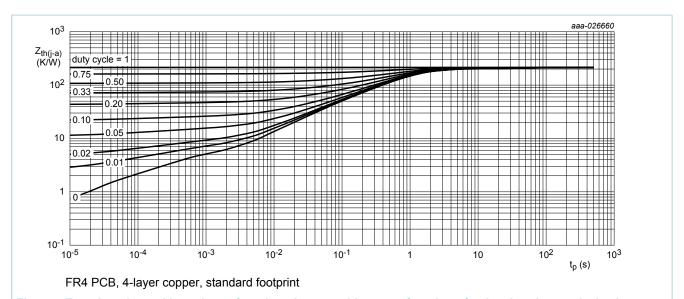


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

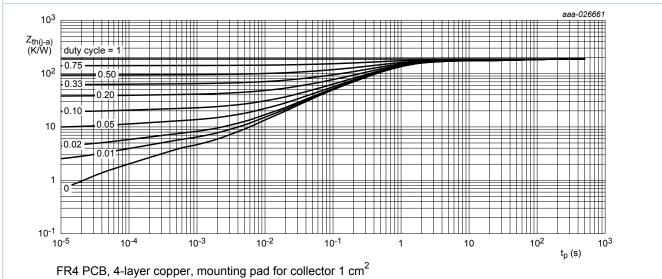


Fig. 6. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{(BR)CBO}	collector-base breakdown voltage	$I_C = -100 \mu A; I_E = 0 A; T_{amb} = 25 °C$		-50	-	-	V
V _{(BR)CEO}	collector-emitter breakdown voltage	I_C = -10 mA; I_B = 0 A; T_{amb} = 25 °C		-50	-	-	V
V _{(BR)EBO}	emitter-base breakdown voltage (collector open)	$I_C = 0 \text{ A}; I_E = -100 \mu\text{A}; T_{amb} = 25 \text{ °C}$		-7	-	-	V
I _{CBO}	collector-base cut-off	V _{CB} = -50 V; I _E = 0 A; T _{amb} = 25 °C		-	-	- V - V - V - 100 nA -5 μA -100 nA -5	nA
	current	V _{CB} = -50 V; I _E = 0 A; T _j = 150 °C		-	-	-5	μA
I _{EBO}	emitter-base cut-off current	V_{EB} = -5 V; I_{C} = 0 A; T_{amb} = 25 °C		-	-	-100	nA
h _{FE}	DC current gain	V_{CE} = -2 V; I_{C} = -100 mA; T_{amb} = 25 °C	[1]	200	-	-	
		V_{CE} = -2 V; I_{C} = -500 mA; T_{amb} = 25 °C	[1]	200	-	-	
		V _{CE} = -2 V; I _C = -1 A; T _{amb} = 25 °C	[1]	200	-	-	
		V _{CE} = -2 V; I _C = -2 A; T _{amb} = 25 °C	[1]	130	-	-	
		V_{CE} = -2 V; I_{C} = -3 A; T_{amb} = 25 °C	[1]	80	-	-	
V _{CEsat}	collector-emitter saturation voltage	I_C = -500 mA; I_B = -50 mA; T_{amb} = 25 °C	[1]	-	-	-90	mV
		I_C = -1 A; I_B = -50 mA; T_{amb} = 25 °C	[1]	-	-	-180	mV
		I_C = -2 A; I_B = -100 mA; T_{amb} = 25 °C	[1]	-	-	-320	mV
		I_C = -2 A; I_B = -200 mA; T_{amb} = 25 °C	[1]	-	-	-270	mV
		I_C = -3 A; I_B = -300 mA; T_{amb} = 25 °C	[1]	-	-	-390	mV
R _{CEsat}	collector-emitter saturation resistance	$I_C = -2 \text{ A}; I_B = -200 \text{ mA}; T_{amb} = 25 \text{ °C}$	[1]	-	-	135	mΩ
V_{BEsat}	base-emitter saturation	I_C = -2 A; I_B = -100 mA; T_{amb} = 25 °C	[1]	-	-	-1.1	V
	voltage	I_C = -3 A; I_B = -300 mA; T_{amb} = 25 °C	[1]	-	-	-1.2	V
V_{BE}	base-emitter voltage	V_{CE} = -2 V; I_{C} = -1 A; T_{amb} = 25 °C	[1]	-	-	-1.2	V
f⊤	transition frequency	V_{CE} = -5 V; I_{C} = -100 mA; f = 100 MHz; T_{amb} = 25 °C		100	-	-	MHz
C _c	collector capacitance	V _{CB} = -10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C		-	-	35	pF

^[1] Pulse test: $t_p \le 300 \ \mu s; \ \delta \le 0.02$

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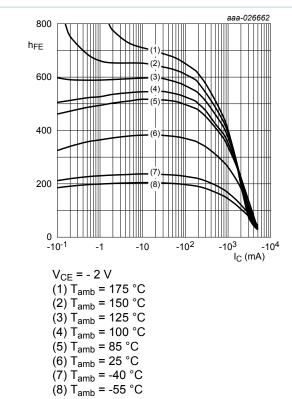
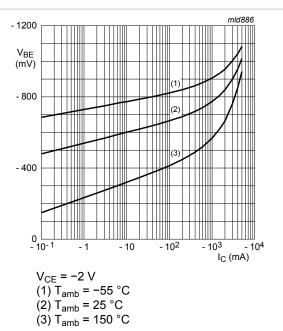


Fig. 7. DC current gain as a function of collector current; typical values



Base-emitter voltage as a function of collector Fig. 8. current; typical values

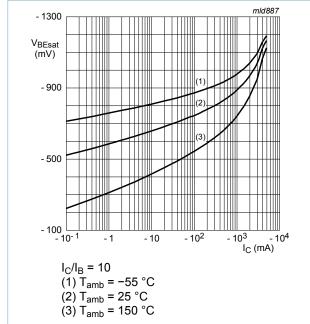
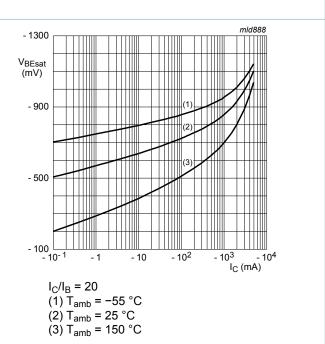


Fig. 9. collector current; typical values



Base-emitter saturation voltage as a function of | Fig. 10. Base-emitter saturation voltage as a function of collector current; typical values

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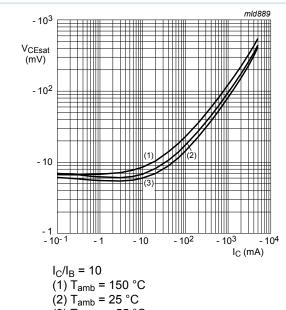
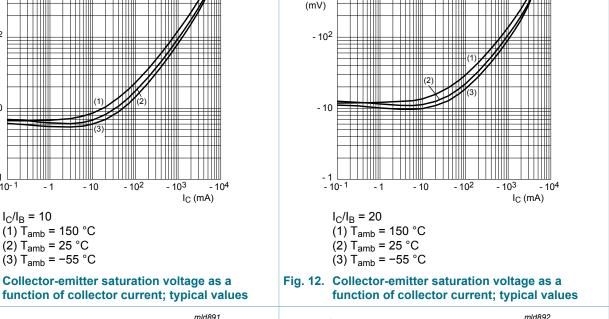


Fig. 11. Collector-emitter saturation voltage as a



- 10³

V_{CEsat}

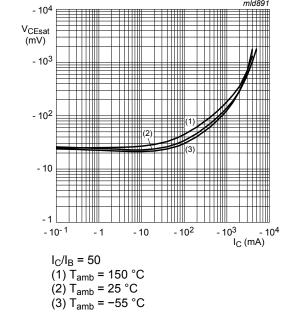


Fig. 13. Collector-emitter saturation voltage as a function of collector current; typical values

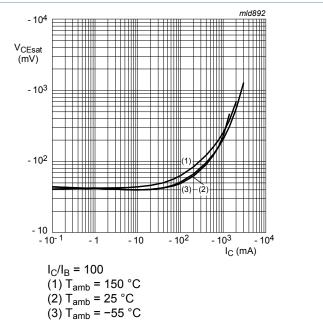
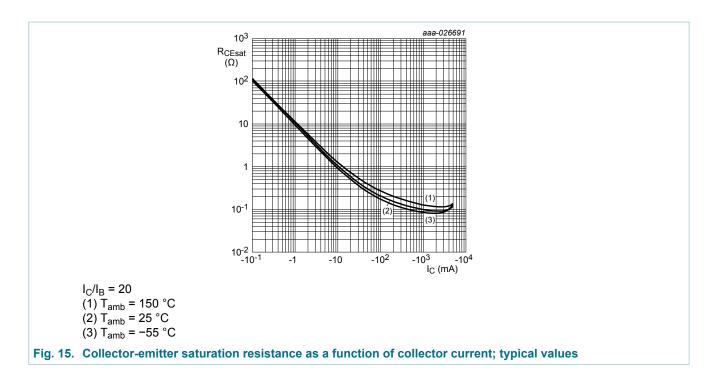


Fig. 14. Collector-emitter saturation voltage as a function of collector current; typical values

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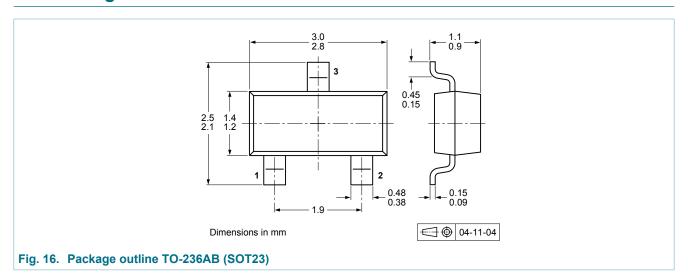


11. Test information

Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

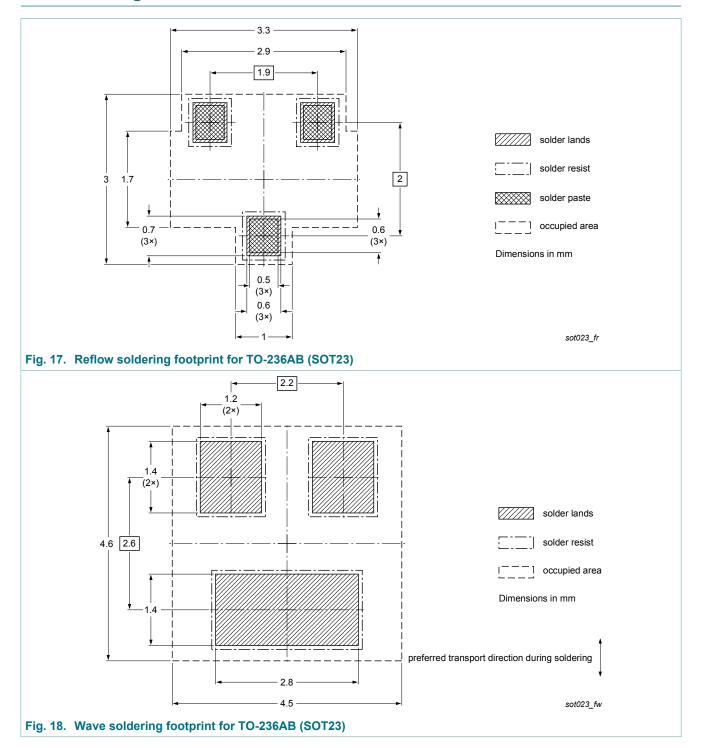
12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBSS5350TH v.1	20170621	Product data sheet	-	-

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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